

isc Silicon NPN Power Transistor

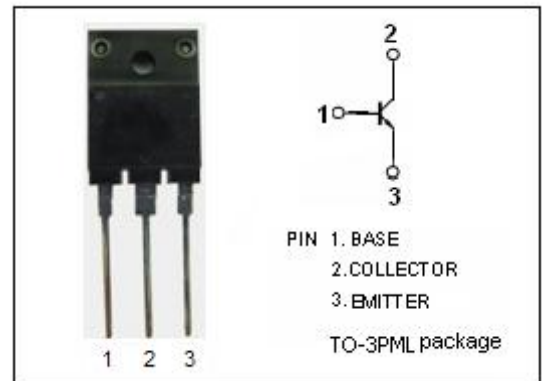
2SC3755

DESCRIPTION

- Collector-Emitter Sustaining Voltage-
: $V_{CEO(SUS)} = 700V(\text{Min})$
- High Switching Speed

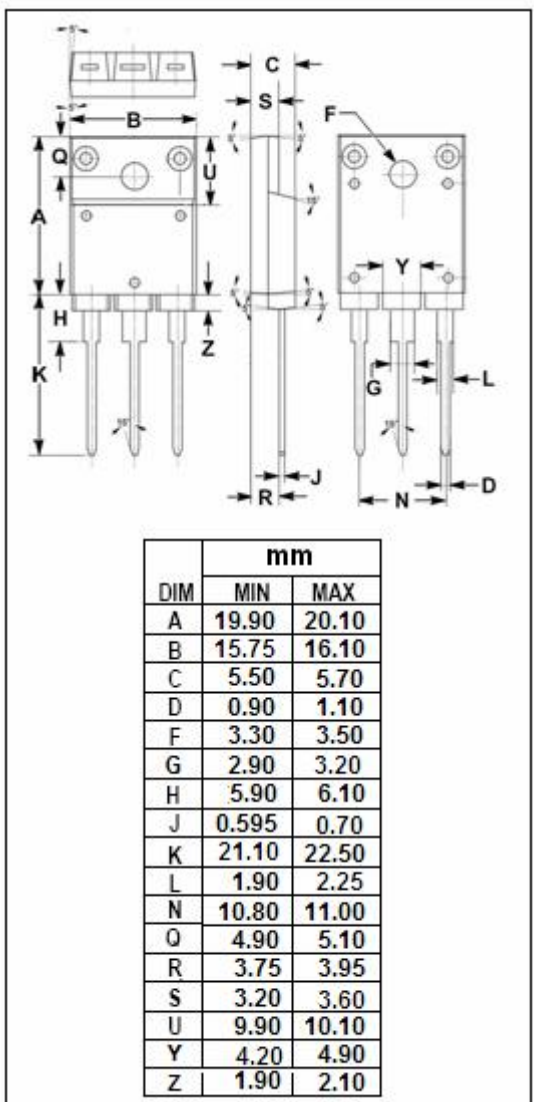
APPLICATIONS

- Designed for use in horizontal deflection circuits of color TV receivers and line operated switch-mode applications



ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	1300	V
V_{CEO}	Collector-Emitter Voltage	700	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current-Continuous	5	A
I_{CM}	Collector Current-Pulse	10	A
I_B	Base Current-Continuous	1.5	A
P_C	Collector Power Dissipation @ $T_c=25^{\circ}\text{C}$	60	W
T_J	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55~150	$^{\circ}\text{C}$



isc Silicon NPN Power Transistor**2SC3755****ELECTRICAL CHARACTERISTICS****T_j=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = 5mA; R _{BE} = ∞	700			V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	I _C = 1mA; I _E = 0	1300			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = 1mA; I _C = 0	7			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 3A; I _B = 0.3A			5.0	V
I _{CBO}	Collector Cutoff Current	V _{CB} = 700V ; I _E = 0			10	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} = 5V; I _C = 0			10	μ A
h _{FE-1}	DC Current Gain	I _C = 0.1A ; V _{CE} = 5V	6		30	
h _{FE-2}	DC Current Gain	I _C = 1A ; V _{CE} = 5V	8	20		